Semiconductor-Metal Transition in Novel Cd₂Os₂O₇*

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Cd₂Os₂O₇ has been prepared for the first time and has the pyrochlore structure with a cubic cell edge of 10.17 Å at room temperature.

* For details see A. W. Sleight, J. L. Gillson, J. F. Weiher, and W. Bindloss, *Solid State Commun* 14, 357 (1974).

Electrical, magnetic, and D.S.C. measurements on single crystals of this compound show a sharp transition at 225 K which we interpret to be an electronic, second-order, metal-semiconductor transition. The low-temperature semiconducting phase is probably antiferromagnetic.